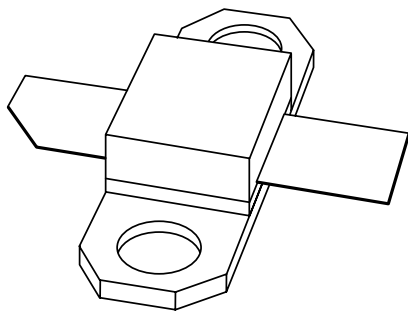


# DATA SHEET



## **BLV2045N** UHF power transistor

Preliminary specification  
Supersedes data of 1999 May 01

2000 Feb 21

## UHF power transistor

## BLV2045N

## FEATURES

- Emitter ballasting resistors for optimum temperature profile
- Gold metallization ensures excellent reliability
- Internal input and output matching for an easy design of wideband circuits.

## APPLICATIONS

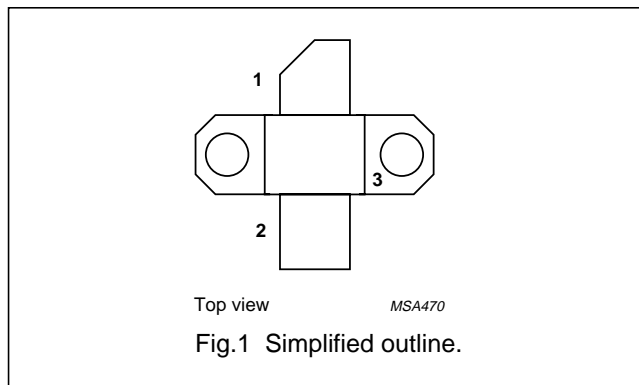
- Common emitter class-AB operation in PCN and PCS applications in the 1800 to 2000 MHz frequency range.

## DESCRIPTION

NPN silicon planar UHF power transistor in a 2-lead SOT390A flange package with a ceramic cap. The emitter is connected to the flange.

## PINNING - SOT390A

PIN	SYMBOL	DESCRIPTION
1	c	collector
2	b	base
3	e	emitter, connected to flange



## QUICK REFERENCE DATA

RF performance at  $T_h = 25\text{ °C}$  in a common emitter test circuit.

MODE OF OPERATION	f (MHz)	$V_{CE}$ (V)	$P_L$ (W)	$G_p$ (dB)	$\eta_c$ (%)	$d_{im}$ (dBc)
CW, class-AB	1990	26	35	typ. 9.5	typ. 43	–
2-tone, class-AB	$f_1 = 1990.0$ ; $f_2 = 1990.1$	26	35 (PEP)	$\geq 9.5$	$\geq 33$	$\leq -30$

## LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{CBO}$	collector-base voltage	open emitter	–	65	V
$V_{CEO}$	collector-emitter voltage	open base	–	27	V
$V_{EBO}$	emitter-base voltage	open collector	–	3	V
$I_C$	collector current (DC)		–	4	A
$I_{C(AV)}$	average collector current		–	4	A
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C}$	–	125	W
$T_{stg}$	storage temperature		–65	+150	°C
$T_j$	operating junction temperature		–	200	°C

## WARNING

## Product and environmental safety - toxic materials

This product contains beryllium oxide. The product is entirely safe provided that the BeO disc is not damaged. All persons who handle, use or dispose of this product should be aware of its nature and of the necessary safety precautions. After use, dispose of as chemical or special waste according to the regulations applying at the location of the user. It must never be thrown out with the general or domestic waste.

## UHF power transistor

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## THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-mb}$	thermal resistance from junction to mounting base	$P_L = 35\text{ W}$ ; $\eta_C = 40\%$ ; $T_{mb} = 25\text{ }^\circ\text{C}$	1.4	K/W
$R_{th\ mb-h}$	thermal resistance from mounting base to heatsink		0.4	K/W

## CHARACTERISTICS

$T_j = 25\text{ }^\circ\text{C}$  unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{(BR)CBO}$	collector-base breakdown voltage	open emitter; $I_C = 20\text{ mA}$	65	–	–	V
$V_{(BR)CEO}$	collector-emitter breakdown voltage	open base; $I_C = 60\text{ mA}$	27	–	–	V
$V_{(BR)EBO}$	emitter-base breakdown voltage	open collector; $I_E = 40\text{ mA}$	3	–	–	V
$I_{CES}$	collector leakage current	$V_{CE} = 26\text{ V}$ ; $V_{BE} = 0$	–	–	4	mA
$h_{FE}$	DC current gain	$V_{CE} = 10\text{ V}$ ; $I_C = 2\text{ A}$	45	–	100	
$C_c$	collector capacitance	$V_{CB} = 26\text{ V}$ ; $I_E = i_e = 0$ ; $f = 1\text{ MHz}$ ; note 1	–	t.b.f.	–	pF
$C_{re}$	feedback capacitance	$V_{CE} = 26\text{ V}$ ; $I_C = 0$ ; $f = 1\text{ MHz}$	–	t.b.f.	–	pF

## Note

1. Capacitance of die only.

## APPLICATION INFORMATION

RF performance at  $T_h = 25\text{ }^\circ\text{C}$  in a common emitter test circuit.

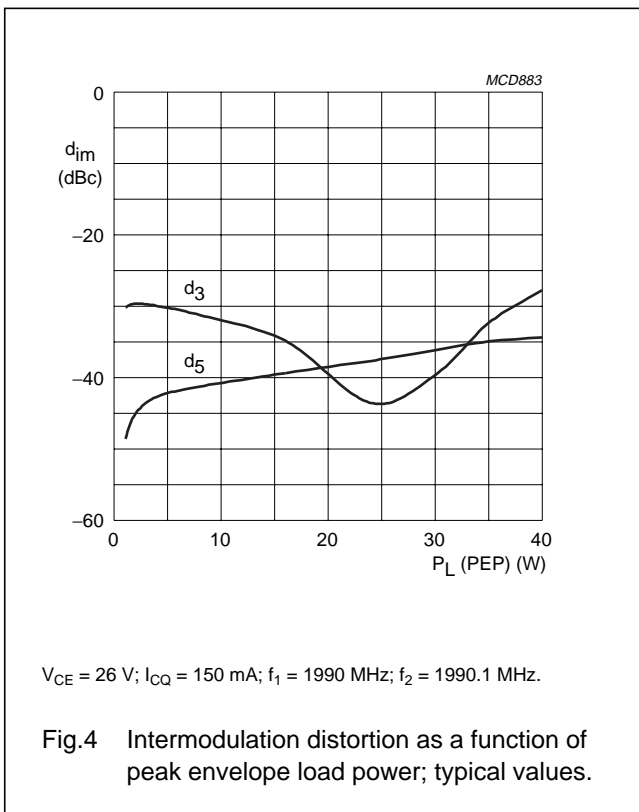
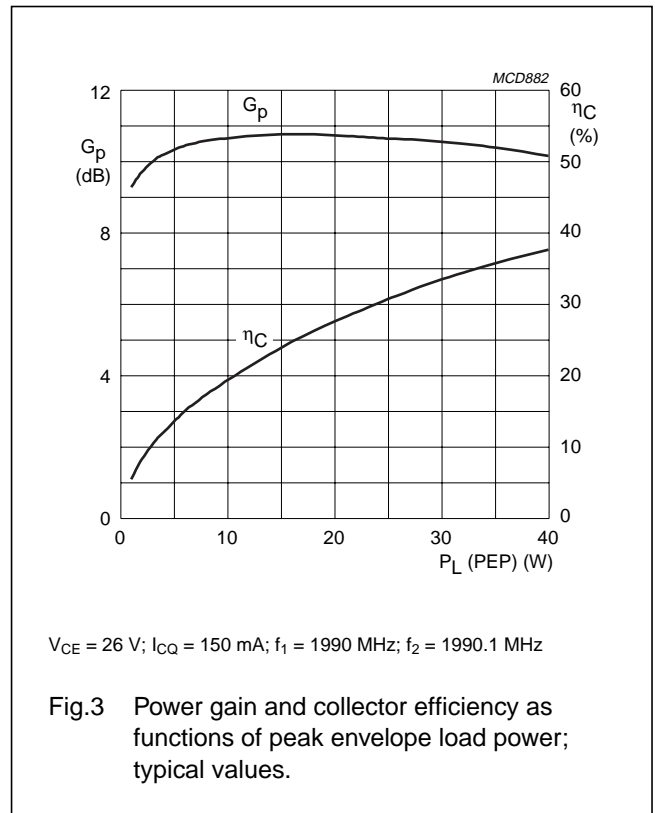
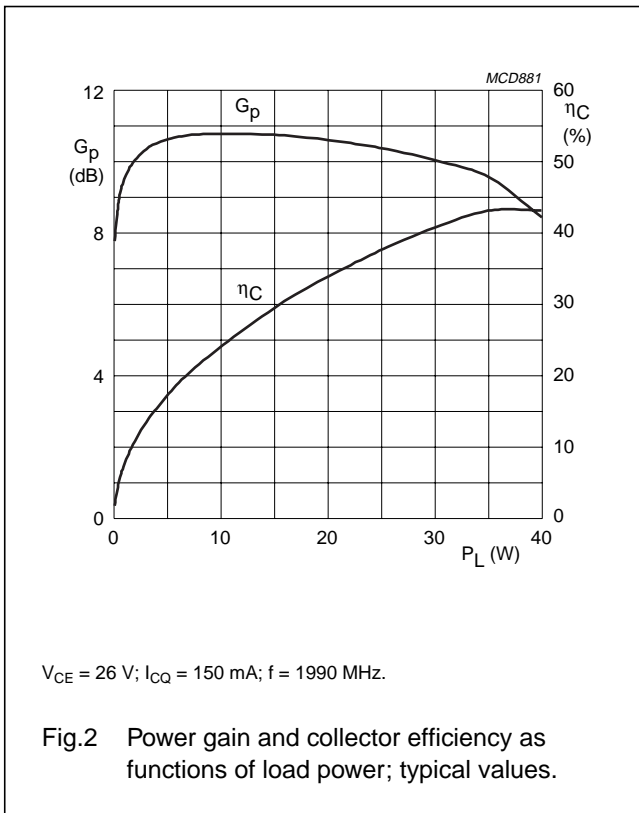
MODE OF OPERATION	f (MHz)	$V_{CE}$ (V)	$I_{CQ}$ (mA)	$P_L$ (W)	$G_p$ (dB)	$\eta_C$ (%)	$d_{im}$ (dBc)
CW, class-AB	1990	26	150	35	typ. 9.5	typ. 43	–
2-tone, class-AB	$f_1 = 1990.0$ ; $f_2 = 1990.1$	26	150	35 (PEP)	$\geq 9.5$ typ. 10.2	$\geq 33$ typ. 35	$\leq -30$ typ. -32

## Ruggedness in class-AB operation

The BLV2045N is capable of withstanding a load mismatch corresponding to  $VSWR = 3 : 1$  through all phases under the following conditions:  $f_1 = 1990.0\text{ MHz}$ ;  $f_2 = 1990.1\text{ MHz}$ ;  $V_{CE} = 26\text{ V}$ ;  $I_{CQ} = 150\text{ mA}$ ;  $P_L = 35\text{ W}$  (PEP);  $T_{mb} = 25\text{ }^\circ\text{C}$ .

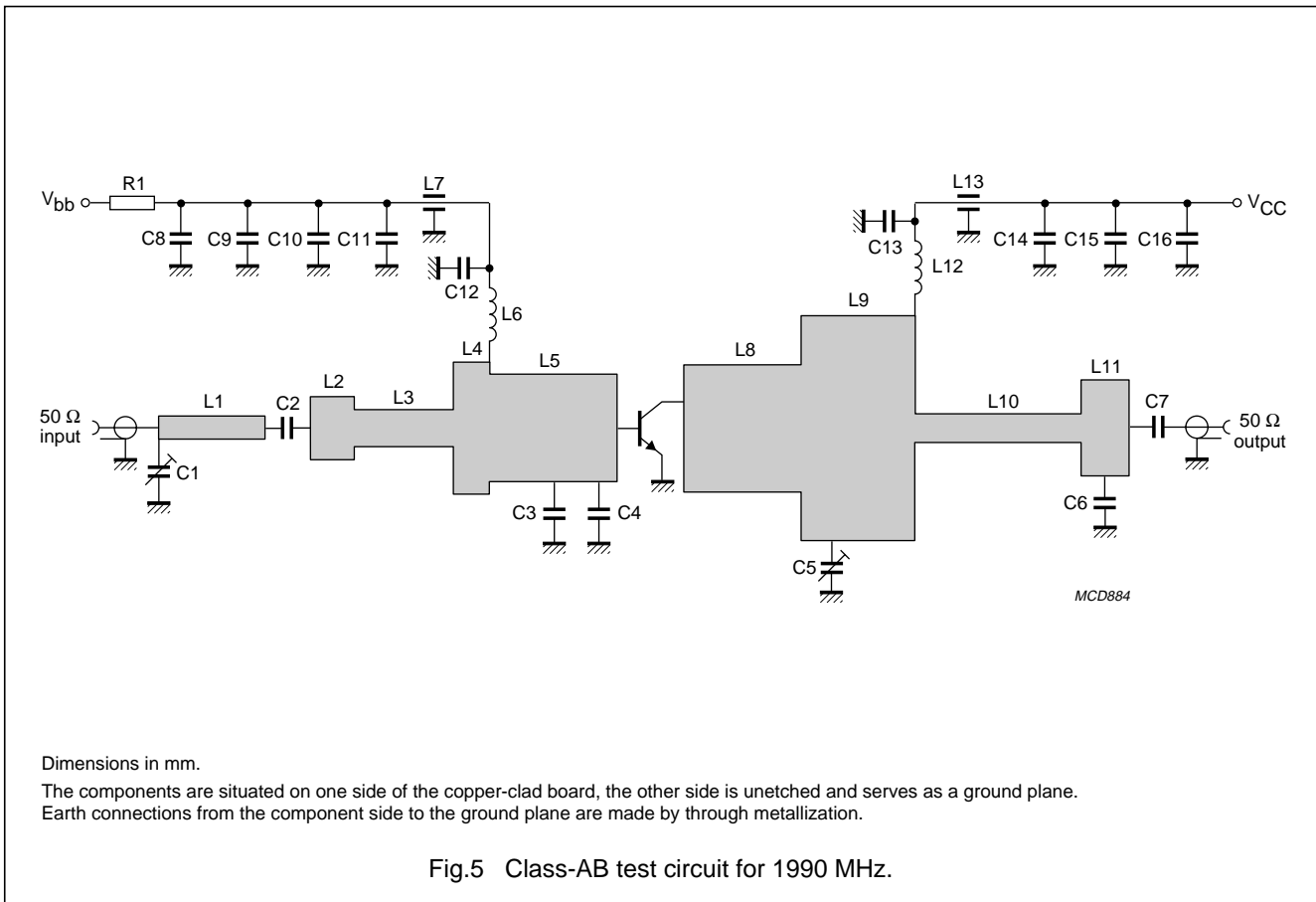
UHF power transistor

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UHF power transistor

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## UHF power transistor

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## List of components (see Figs 5 and 6)

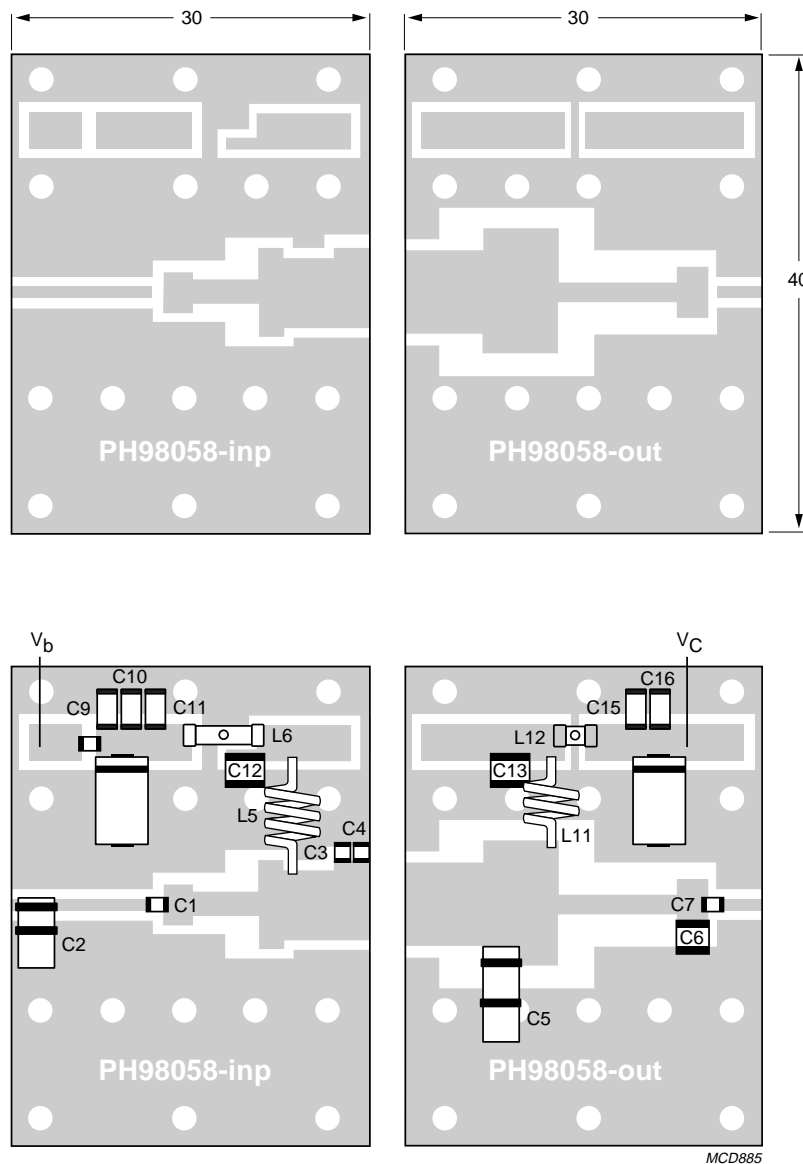
COMPONENT	DESCRIPTION	VALUE	DIMENSIONS
C1	Tekelec variable capacitor; type AT37281	0.4 to 2.5 pF	
C2, C7	multilayer ceramic chip capacitor; note 1	30 pF	
C3	multilayer ceramic chip capacitor; note 2	2.4 pF	
C4	multilayer ceramic chip capacitor; note 2	1.8 pF	
C5	Tekelec variable capacitor; type AT37271	0.6 to 4.5 pF	
C6	multilayer ceramic chip capacitor; note 2	1.3 pF	
C8, C14	tantalum SMD capacitor	35 V; 10 $\mu$ F	
C9, C10, C11, C15, C16	multilayer ceramic chip capacitor	100 nF	
C12, C13	multilayer ceramic chip capacitor; note 2	20 pF	
L1	stripline; note 3	50 $\Omega$	8 x 1 mm
L2	stripline; note 3	20.5 $\Omega$	2.5 x 3.5 mm
L3	stripline; note 3	29.8 $\Omega$	5.6 x 2.1 mm
L4	stripline; note 3	11 $\Omega$	2.0 x 7.4 mm
L5	stripline; note 3	13.2 $\Omega$	7.2 x 6.0 mm
L6	5 turns enamelled 1 mm copper wire		int. dia. = 3.3 mm; length = 6 mm
L7	EMI filter; type NFM61RH20T332	3300 pF	
L8	stripline; note 3	11.5 $\Omega$	6.6 x 7.1 mm
L9	stripline; note 3	6.9 $\Omega$	6.4 x 12.6 mm
L10	stripline; note 3	35.8 $\Omega$	9.9 x 1.6 mm
L11	stripline; note 3	14.4 $\Omega$	2.7 x 5.4 mm
L12	2 turns enamelled 1 mm copper wire		int. dia. = 3.3 mm; length = 2.5 mm
L13	EMI filter; type NFM60RH20T152	1500 pF	
R1	chip resistor	2.2 $\Omega$	

## Notes

1. American Technical Ceramics type 100A or capacitor of same quality.
2. American Technical Ceramics type 100B or capacitor of same quality.
3. The striplines are on a double copper-clad printed-circuit board:  $\epsilon_r = 6.15$ ; thickness 0.64mm.

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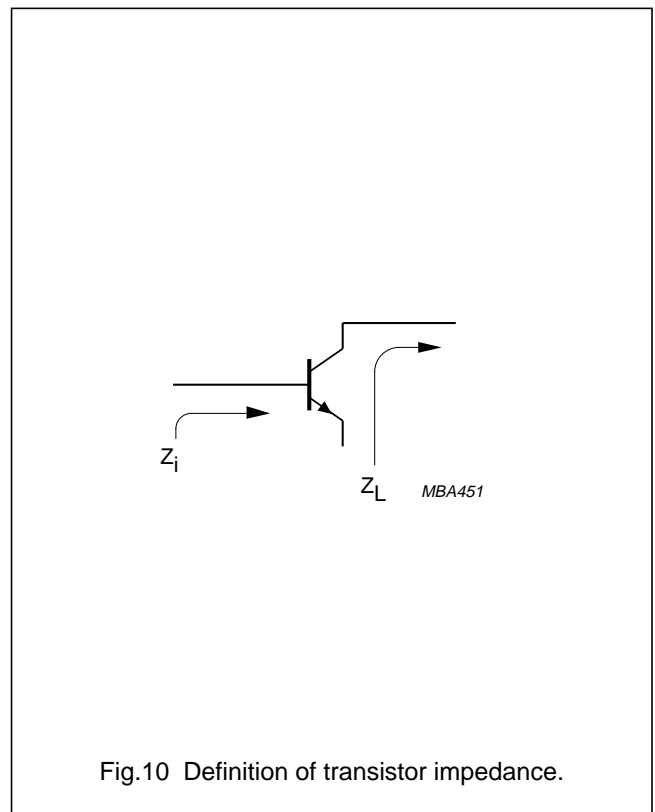
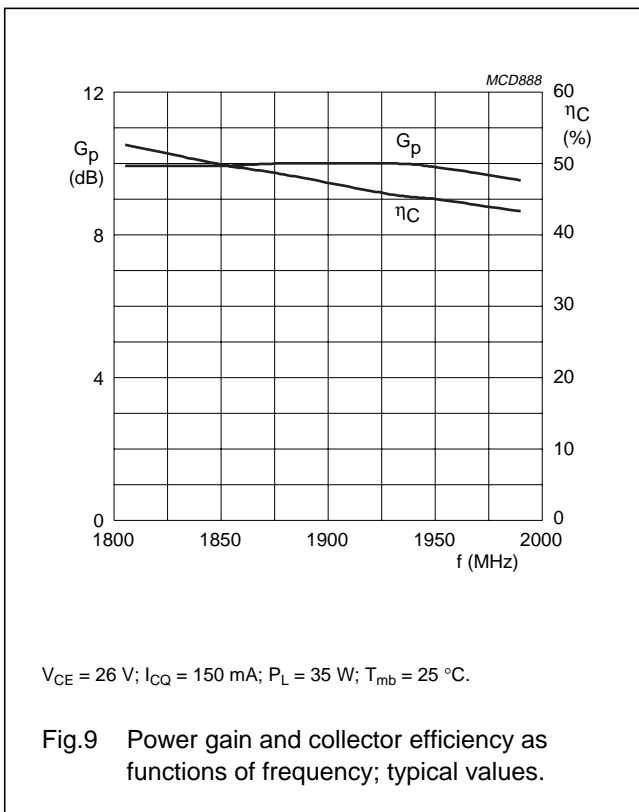
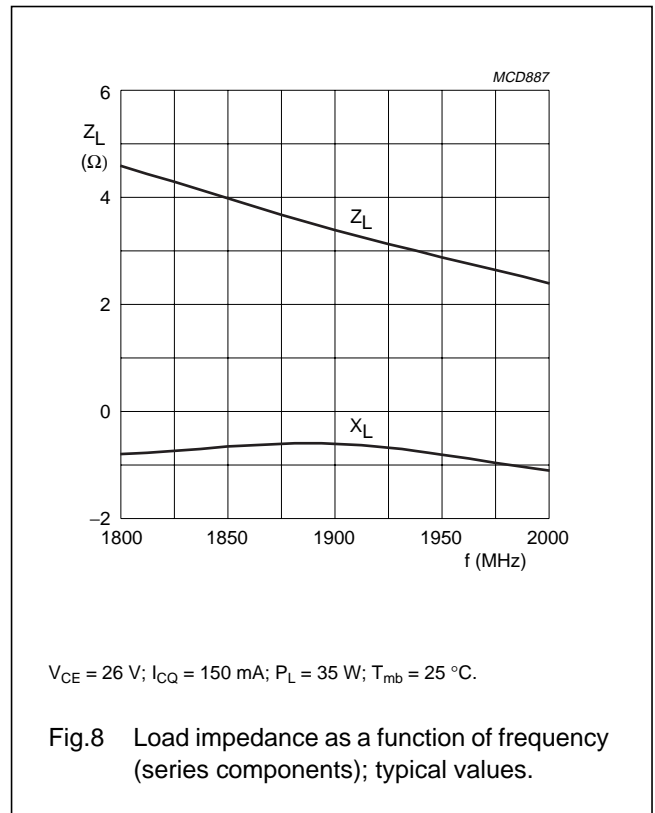
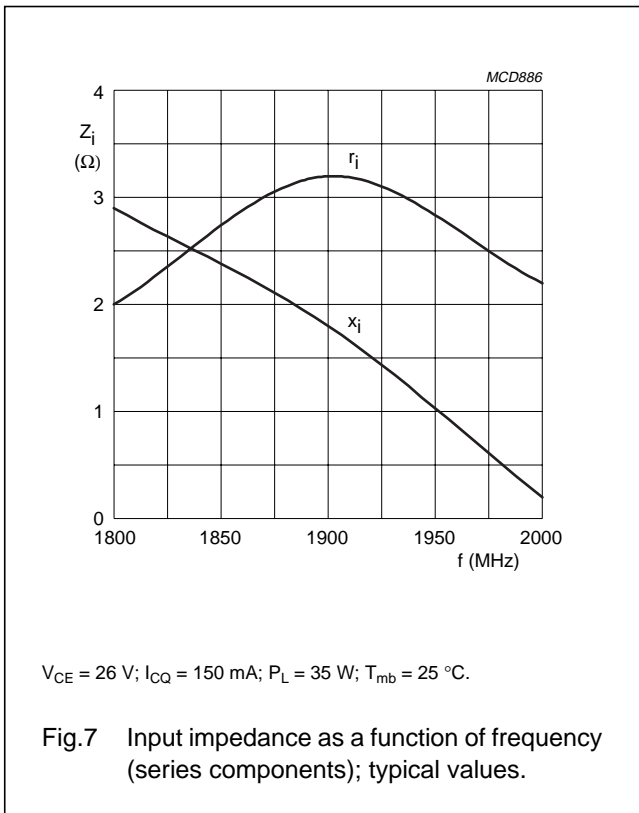
Dimensions in mm.

The components are situated on one side of the copper-clad board, the other side is unetched and serves as a ground plane. Earth connections from the component side to the ground plane are made by through metallization.

Fig.6 Printed-circuit board and component layout for class-AB broadband test circuit.

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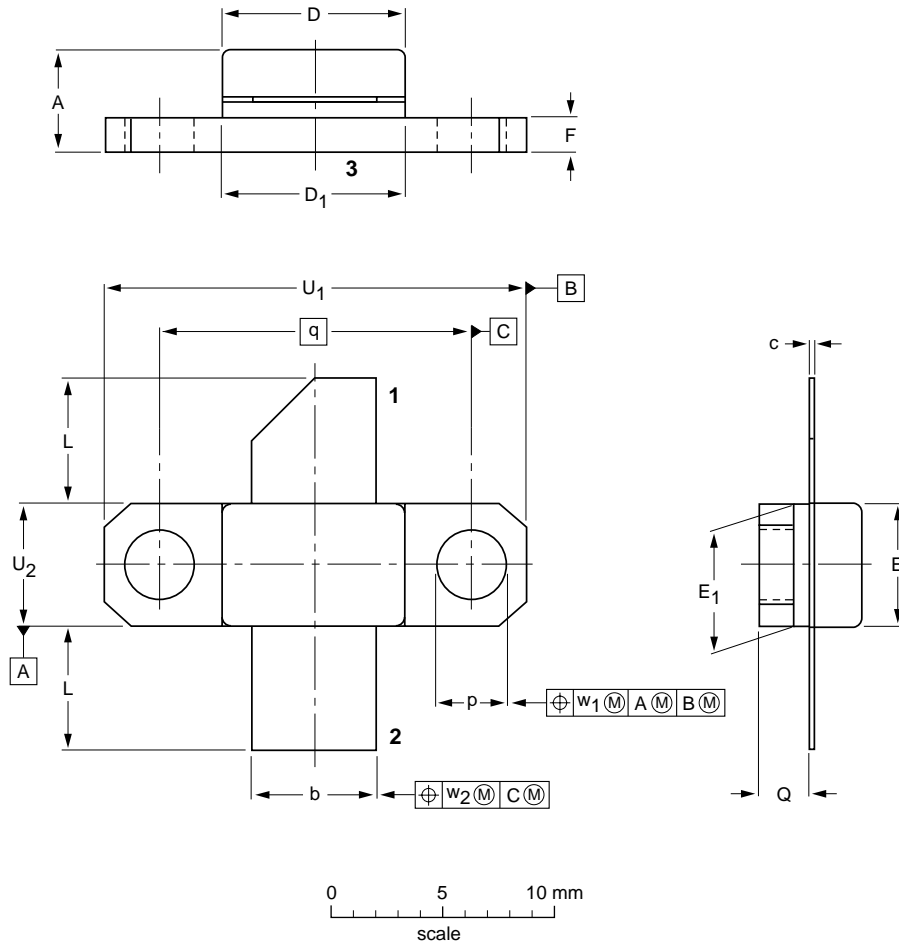
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PACKAGE OUTLINE

Flanged ceramic package; 2 mounting holes; 2 leads

SOT390A



DIMENSIONS (millimetre dimensions are derived from the original inch dimensions)

UNIT	A	b	c	D	D <sub>1</sub>	E	E <sub>1</sub>	F	L	p	Q	q	U <sub>1</sub>	U <sub>2</sub>	w <sub>1</sub>	w <sub>2</sub>
mm	5.03 4.22	5.72 5.46	0.16 0.10	8.18 8.08	8.26 8.00	6.40 6.30	6.43 6.17	1.66 1.39	6.10 5.33	3.43 3.17	2.32 2.00	14.22	19.03 18.77	6.43 6.17	0.25	0.51
inches	0.198 0.166	0.225 0.215	0.006 0.004	0.322 0.318	0.325 0.315	0.252 0.248	0.253 0.243	0.065 0.055	0.24 0.21	0.135 0.125	0.091 0.079	0.560	0.749 0.739	0.253 0.243	0.010	0.020

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT390A						99-03-29

## UHF power transistor

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**DEFINITIONS**

<b>Data Sheet Status</b>	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
<b>Limiting values</b>	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
<b>Application information</b>	
Where application information is given, it is advisory and does not form part of the specification.	

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**Argentina:** see South America

**Australia:** 3 Figtree Drive, HOMEBUSH, NSW 2140,  
Tel. +61 2 9704 8141, Fax. +61 2 9704 8139

**Austria:** Computerstr. 6, A-1101 WIEN, P.O. Box 213,  
Tel. +43 1 60 101 1248, Fax. +43 1 60 101 1210

**Belarus:** Hotel Minsk Business Center, Bld. 3, r. 1211, Volodarski Str. 6,  
220050 MINSK, Tel. +375 172 20 0733, Fax. +375 172 20 0773

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**China/Hong Kong:** 501 Hong Kong Industrial Technology Centre,  
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**Czech Republic:** see Austria

**Denmark:** Sydhavnsgade 23, 1780 COPENHAGEN V,  
Tel. +45 33 29 3333, Fax. +45 33 29 3905

**Finland:** Sinikalliontie 3, FIN-02630 ESPOO,  
Tel. +358 9 615 800, Fax. +358 9 6158 0920

**France:** 51 Rue Carnot, BP317, 92156 SURESNES Cedex,  
Tel. +33 1 4099 6161, Fax. +33 1 4099 6427

**Germany:** Hammerbrookstraße 69, D-20097 HAMBURG,  
Tel. +49 40 2353 60, Fax. +49 40 2353 6300

**Hungary:** see Austria

**India:** Philips INDIA Ltd, Band Box Building, 2nd floor,  
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**Indonesia:** PT Philips Development Corporation, Semiconductors Division,  
Gedung Philips, Jl. Buncit Raya Kav.99-100, JAKARTA 12510,  
Tel. +62 21 794 0040 ext. 2501, Fax. +62 21 794 0080

**Ireland:** Newstead, Clonskeagh, DUBLIN 14,  
Tel. +353 1 7640 000, Fax. +353 1 7640 200

**Israel:** RAPAC Electronics, 7 Kehilat Saloniki St, PO Box 18053,  
TEL AVIV 61180, Tel. +972 3 645 0444, Fax. +972 3 649 1007

**Italy:** PHILIPS SEMICONDUCTORS, Via Casati, 23 - 20052 MONZA (MI),  
Tel. +39 039 203 6838, Fax +39 039 203 6800

**Japan:** Philips Bldg 13-37, Kohnan 2-chome, Minato-ku,  
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Tel. +60 3 750 5214, Fax. +60 3 757 4880

**Mexico:** 5900 Gateway East, Suite 200, EL PASO, TEXAS 79905,  
Tel. +9-5 800 234 7381, Fax +9-5 800 943 0087

**Middle East:** see Italy

**Netherlands:** Postbus 90050, 5600 PB EINDHOVEN, Bldg. VB,  
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**New Zealand:** 2 Wagener Place, C.P.O. Box 1041, AUCKLAND,  
Tel. +64 9 849 4160, Fax. +64 9 849 7811

**Norway:** Box 1, Manglerud 0612, OSLO,  
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**Philippines:** Philips Semiconductors Philippines Inc.,  
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Metro MANILA, Tel. +63 2 816 6380, Fax. +63 2 817 3474

**Poland:** Al.Jerozolimskie 195 B, 02-222 WARSAW,  
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Tel. +27 11 471 5401, Fax. +27 11 471 5398

**South America:** Al. Vicente Pinzon, 173, 6th floor,  
04547-130 SÃO PAULO, SP, Brazil,  
Tel. +55 11 821 2333, Fax. +55 11 821 2382

**Spain:** Balmes 22, 08007 BARCELONA,  
Tel. +34 93 301 6312, Fax. +34 93 301 4107

**Sweden:** Kottbygatan 7, Akalla, S-16485 STOCKHOLM,  
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**Switzerland:** Allmendstrasse 140, CH-8027 ZÜRICH,  
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ISTANBUL, Tel. +90 216 522 1500, Fax. +90 216 522 1813

**Ukraine:** PHILIPS UKRAINE, 4 Patrice Lumumba str., Building B, Floor 7,  
252042 KIEV, Tel. +380 44 264 2776, Fax. +380 44 268 0461

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MIDDLESEX UB3 5BX, Tel. +44 208 730 5000, Fax. +44 208 754 8421

**United States:** 811 East Arques Avenue, SUNNYVALE, CA 94088-3409,  
Tel. +1 800 234 7381, Fax. +1 800 943 0087

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